

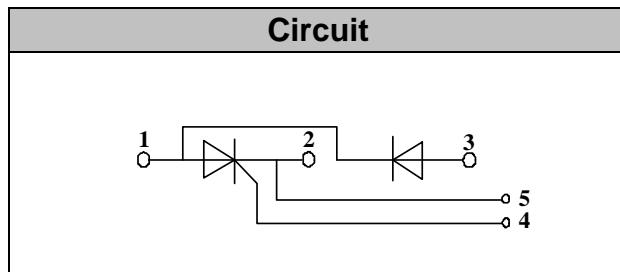


## Thyristor/Diode Modules

**V<sub>RRM</sub> / V<sub>DRM</sub>** 800 to 1800V  
**I<sub>FAV</sub> / I<sub>TAV</sub>** 130A

### Applications

- Power Converters
- Lighting Control
- DC Motor Control and Drives
- Heat and temperature control



### Features

- International standard package
- High Surge Capability
- Glass passivated chip
- Simple Mounting
- Heat transfer through aluminum oxide DBC ceramic isolated metal baseplate
- UL recognized applied for file no. E360040

### Module Type

TYPE	V <sub>RRM</sub> /V <sub>DRM</sub>	V <sub>RSM</sub>
MT130CB08T2	800V	900V
MT130CB12T2	1200V	1300V
MT130CB16T2	1600V	1700V
MT130CB18T2	1800V	1900V

### ◆Diode

### Maximum Ratings

Symbol	Item	Conditions	Values	Units
I <sub>D</sub>	Output Current(D.C.)	T <sub>c</sub> =85°C	130	A
I <sub>FSM</sub>	Surge forward current	t=10mS T <sub>vj</sub> =45°C	4700	A
i <sup>2</sup> t	Circuit Fusing Consideration		110000	A <sup>2</sup> s
V <sub>Isol</sub>	Isolation Breakdown Voltage(R.M.S)	a.c.50HZ;r.m.s.;1min	3000	V
T <sub>vj</sub>	Operating Junction Temperature		-40 to +125	°C
T <sub>stg</sub>	Storage Temperature		-40 to +125	°C
M <sub>t</sub>	Mounting Torque	To terminals(M6)	3±15%	Nm
M <sub>s</sub>		To heatsink(M6)	5±15%	Nm
Weight	Module (Approximately)		165	g

### Thermal Characteristics

Symbol	Item	Conditions	Values	Units
R <sub>th(j-c)</sub>	Thermal Impedance, max.	Junction to Case	0.09	°C/W
R <sub>th(c-s)</sub>	Thermal Impedance, max.	Case to Heatsink	0.05	°C/W

### Electrical Characteristics

Symbol	Item	Conditions	Values			Units
			Min.	Typ.	Max.	
V <sub>F</sub> M	Forward Voltage Drop, max.	T=25°C I <sub>F</sub> =500A			1.80	V
I <sub>RRM</sub>	Repetitive Peak Reverse Current, max.	T <sub>vj</sub> =25°C V <sub>RD</sub> =V <sub>RRM</sub> T <sub>vj</sub> =125°C V <sub>RD</sub> =V <sub>RRM</sub>		≤0.5 ≤9		mA mA



## ◆Thyristor

## Maximum Ratings

Symbol	Item	Conditions	Values	Units
$I_{TAV}$	Average On-State Current	Sine 180°; $T_c=85^\circ\text{C}$	130	A
$I_{TSM}$	Surge On-State Current	$T_{VJ}=45^\circ\text{C}$ t=10ms, sine $T_{VJ}=125^\circ\text{C}$ t=10ms, sine	4700 4000	A
$i^2t$	Circuit Fusing Consideration	$T_{VJ}=45^\circ\text{C}$ t=10ms, sine $T_{VJ}=125^\circ\text{C}$ t=10ms, sine	110000 80000	A2s
Visol	Isolation Breakdown Voltage(R.M.S)	a.c.50HZ;r.m.s.;1min	3000	V
$T_{VJ}$	Operating Junction Temperature		-40 to +130	°C
$T_{STG}$	Storage Temperature		-40 to +125	°C
Mt	Mounting Torque	To terminals(M6)	$3 \pm 15\%$	Nm
Ms		To heatsink(M6)	$5 \pm 15\%$	Nm
$di/dt$	Critical Rate of Rise of On-State Current	$T_{VJ}=T_{VJM}$ , $2/3V_{DRM}$ , $I_G=500\text{mA}$ $Tr<0.5\mu\text{s}, tp>6\mu\text{s}$	200	A/us
$dv/dt$	Critical Rate of Rise of Off-State Voltage, min.	$T_J=T_{VJM}$ , $2/3V_{DRM}$ linear voltage rise	1000	V/us
a	Maximum allowable acceleration		50	$\text{m/s}^2$

## Thermal Characteristics

Symbol	Item	Conditions	Values	Units
$R_{th(j-c)}$	Thermal Impedance, max.	Junction to Case	0.18	°C/W
$R_{th(c-s)}$	Thermal Impedance, max.	Case to Heatsink	0.10	°C/W

## Electrical Characteristics

Symbol	Item	Conditions	Values			Units
			Min.	Typ.	Max.	
$V_{TM}$	Peak On-State Voltage, max.	$T=25^\circ\text{C}$ $I_T=500\text{A}$			1.8	V
$I_{RRM}/I_{DRM}$	Repetitive Peak Reverse Current, max. / Repetitive Peak Off-State Current, max.	$T_{VJ}=T_{VJM}$ , $V_R=V_{RRM}$ , $V_D=V_{DRM}$			40	mA
$V_{TO}$	On state threshold voltage	For power-loss calculations only ( $T_{VJ}=125^\circ\text{C}$ )			1	V
$r_T$	Value of on-state slope resistance, max	$T_{VJ}=T_{VJM}$			1.6	$\text{m}\Omega$
$V_{GT}$	Gate Trigger Voltage, max.	$T_{VJ}=25^\circ\text{C}$ , $V_D=6\text{V}$			3	V
$I_{GT}$	Gate Trigger Current, max.	$T_{VJ}=25^\circ\text{C}$ , $V_D=6\text{V}$			150	mA
$V_{GD}$	Non-triggering gate voltage, max.	$T_{VJ}=125^\circ\text{C}$ , $V_D=2/3V_{DRM}$			0.25	V
$I_{GD}$	Non-triggering gate current, max.	$T_{VJ}=125^\circ\text{C}$ , $V_D=2/3V_{DRM}$			10	mA
$I_L$	Latching current, max.	$T_{VJ}=25^\circ\text{C}$ , $R_G=33\Omega$	300	1000		mA
$I_H$	Holding current, max.	$T_{VJ}=25^\circ\text{C}$ , $V_D=6\text{V}$	150	400		mA
$tgd$	Gate controlled delay time	$T_{VJ}=25^\circ\text{C}$ , $I_G=1\text{A}$ , $diG/dt=1\text{A/us}$			1	us
$tq$	Circuit commutated turn-off time	$T_{VJ}=T_{VJM}$			100	us

## Performance Curves

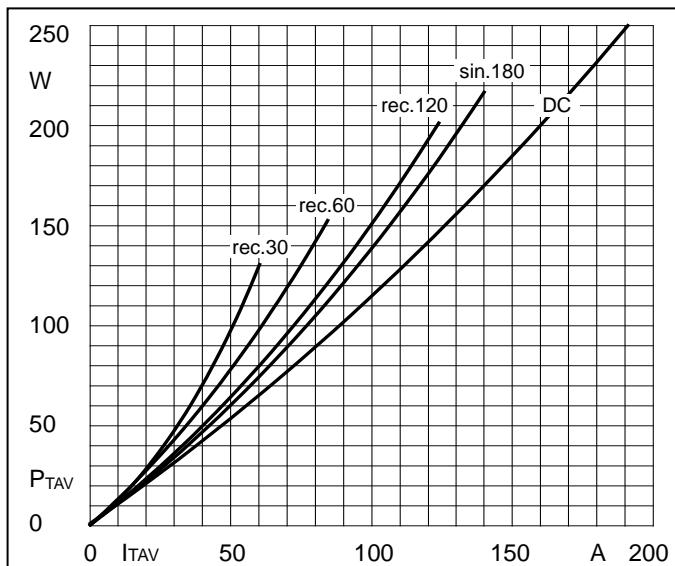


Fig1. Power dissipation

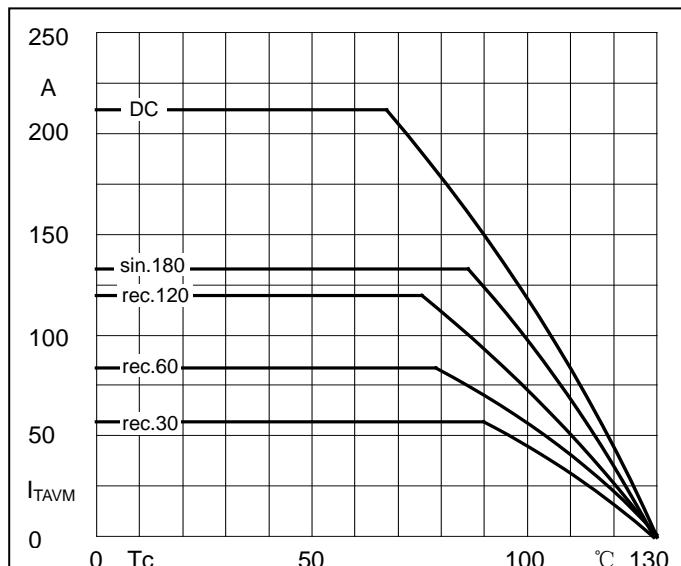


Fig2. Forward Current Derating Curve

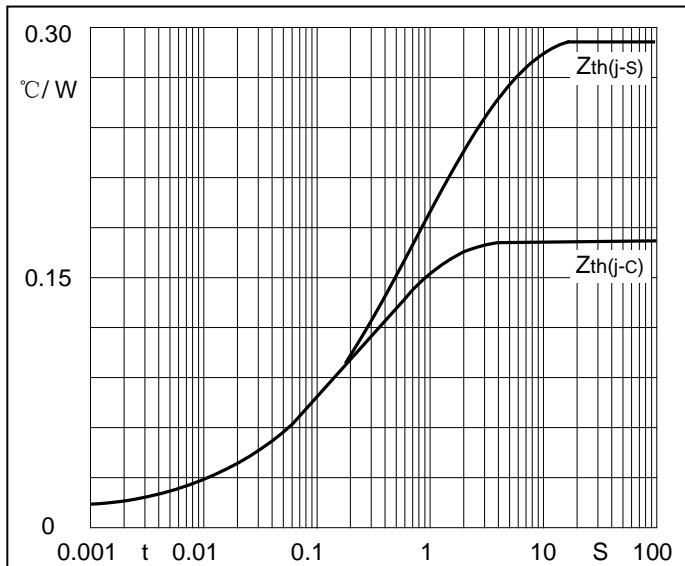


Fig3. Transient thermal impedance

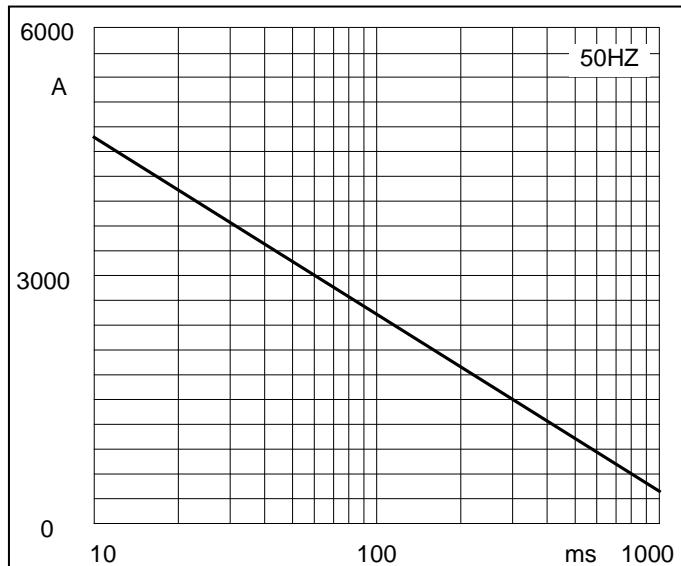


Fig4. Max Non-Repetitive Forward Surge Current

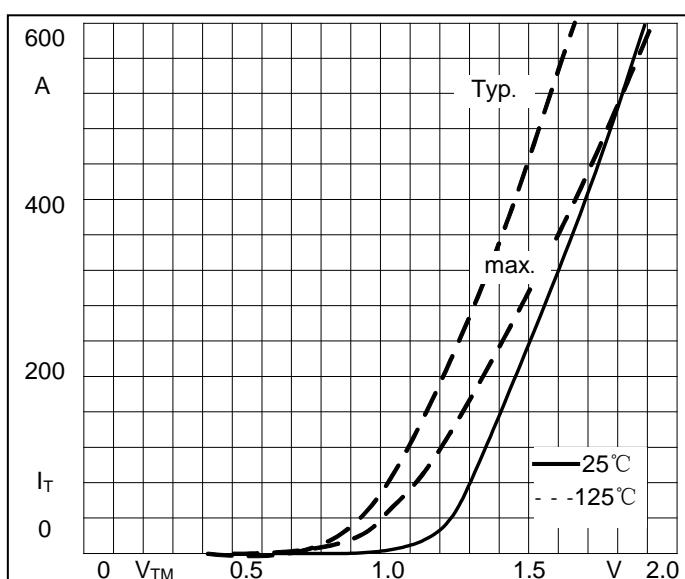


Fig5. Forward Characteristics

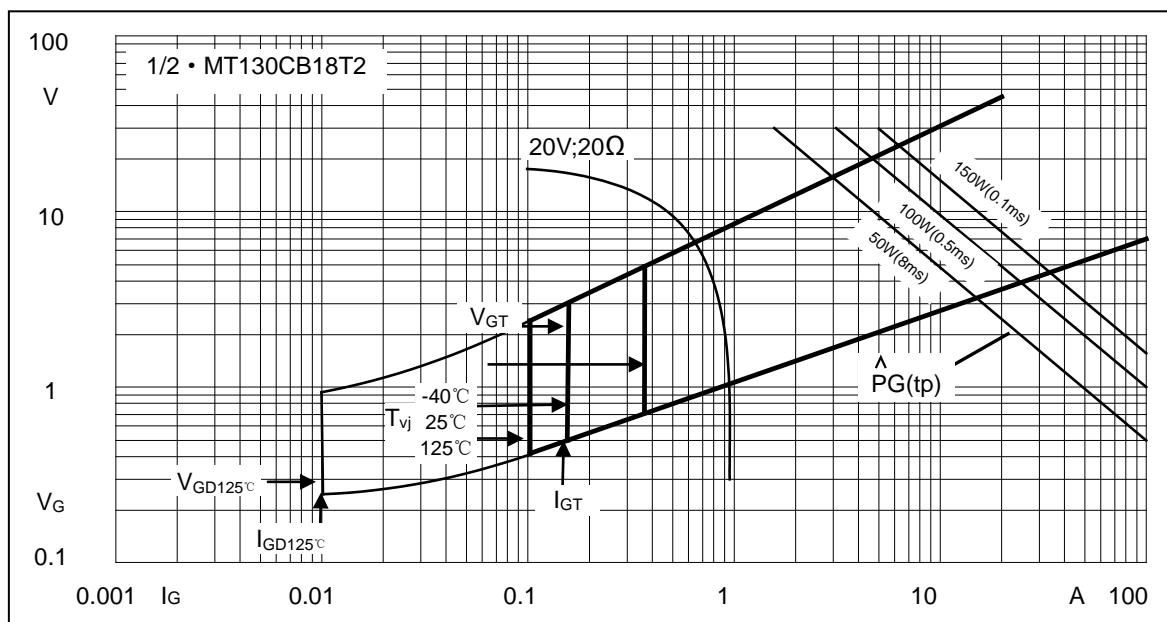
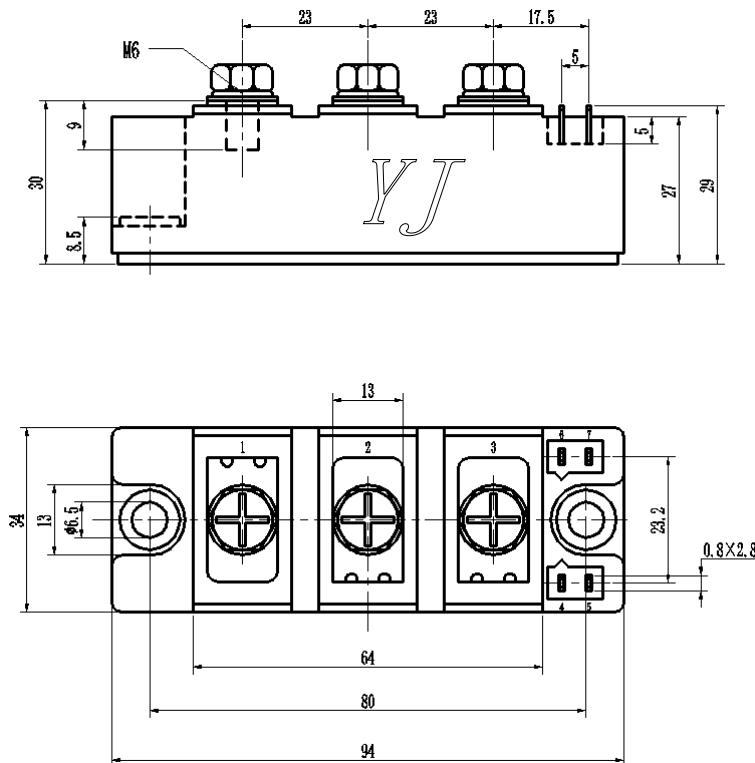


Fig6. Gate trigger Characteristics

### Package Outline Information

#### CASE: T2



Dimensions in mm